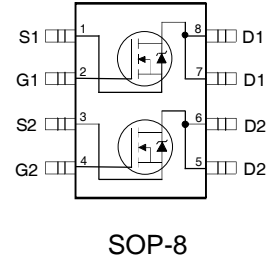


**Description**

The SOP-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infra red, or wave soldering techniques. Power dissipation of greater than 0.8W is possible in a typical PCB mount application.



- Generation V Technology
- Ultra Low On-Resistance
- Dual N-Channel Mosfet
- Surface Mount
- Dynamic dv/dt Rating
- Fast Switching
- Lead-Free

**Features**

- $V_{DS} (V) = 55V$
- $I_D = 4.7A (V_{GS}=10V)$
- $R_{DS(ON)} < 30m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 45m\Omega (V_{GS} = 4.5V)$

**Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_{DS}$	Drain- Source Voltage	55	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	4.7	A
$I_D @ T_C = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	3.8	
$I_{DM}$	Pulsed Drain Current ①	38	
$P_D @ T_C = 25^\circ C$	Power Dissipation	2.0	W
$P_D @ T_C = 70^\circ C$	Power Dissipation	1.3	
	Linear Derating Factor	0.016	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$V_{GSM}$	Gate-to-Source Voltage Single Pulse $tp < 10\mu s$	30	V
$E_{AS}$	Single Pulse Avalanche Energy ②	72	
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	°C

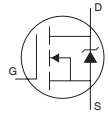
**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ⑤		62.5	°C/W

**Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	55			V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient		0.059		V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance			30	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.7A ④
				45		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.8A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.0			V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	7.9			S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 4.5A
I <sub>DSS</sub>	Drain-to-Source Leakage Current			2.0	μA	V <sub>DS</sub> = 55V, V <sub>GS</sub> = 0V
				25		V <sub>DS</sub> = 55V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 55°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage			-100	nA	V <sub>GS</sub> = -20V
	Gate-to-Source Reverse Leakage			100		V <sub>GS</sub> = 20V
Q <sub>g</sub>	Total Gate Charge		24	36	nC	I <sub>D</sub> = 4.5A
Q <sub>gs</sub>	Gate-to-Source Charge		2.3	3.4		V <sub>DS</sub> = 44V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge		7.0	10		V <sub>GS</sub> = 10V, See Fig. 10 ④
t <sub>d(on)</sub>	Turn-On Delay Time		8.3	12		V <sub>DD</sub> = 28V
t <sub>r</sub>	Rise Time		3.2	4.8	ns	I <sub>D</sub> = 1.0A
t <sub>d(off)</sub>	Turn-Off Delay Time		32	48		R <sub>G</sub> = 6.0Ω
t <sub>f</sub>	Fall Time		13	20		R <sub>D</sub> = 16Ω, ④
C <sub>iss</sub>	Input Capacitance		740		pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance		190			V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance		71			f = 1.0MHz, See Fig. 9

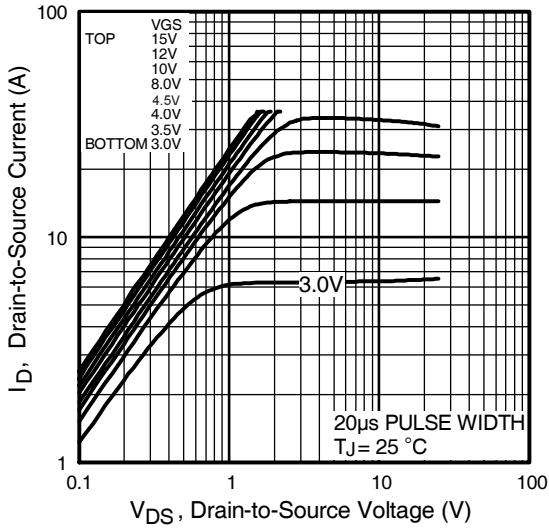
**Source-Drain Ratings and Characteristics**

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)			2.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①			38		
V <sub>SD</sub>	Diode Forward Voltage			1.2	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 2.0A, V <sub>GS</sub> = 0V ⑤
t <sub>rr</sub>	Reverse Recovery Time		60	90	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 2.0A
Q <sub>rr</sub>	Reverse Recovery Charge		120	170	nC	di/dt = -100A/μs ③

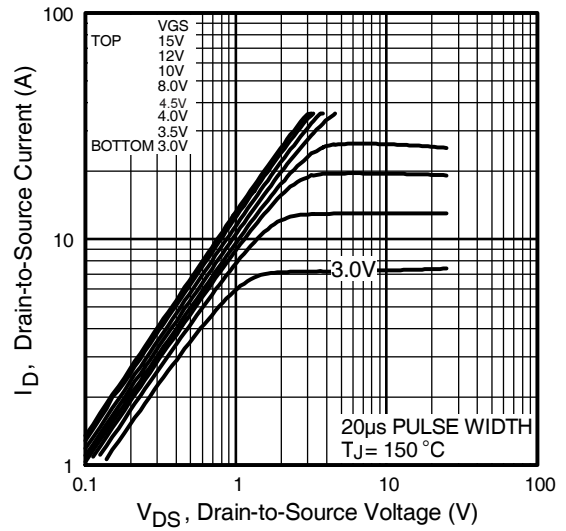
**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② Starting T<sub>J</sub> = 25°C, L = 6.5mH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 4.7A. (See Figure 8)
- ③ I<sub>SD</sub> ≤ 4.7A, di/dt ≤ 220A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ 150°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ When mounted on 1 inch square copper board, t < 10 sec

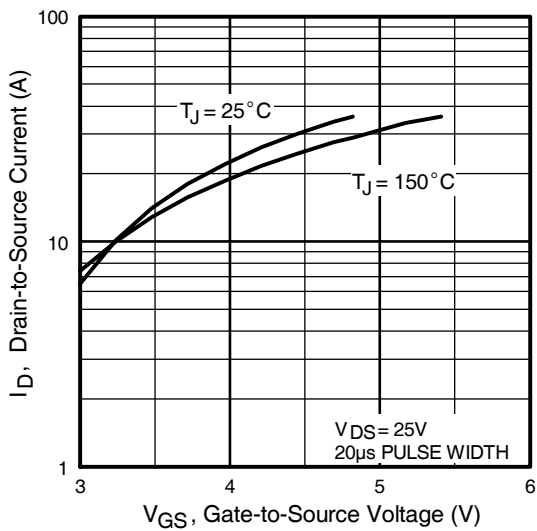
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



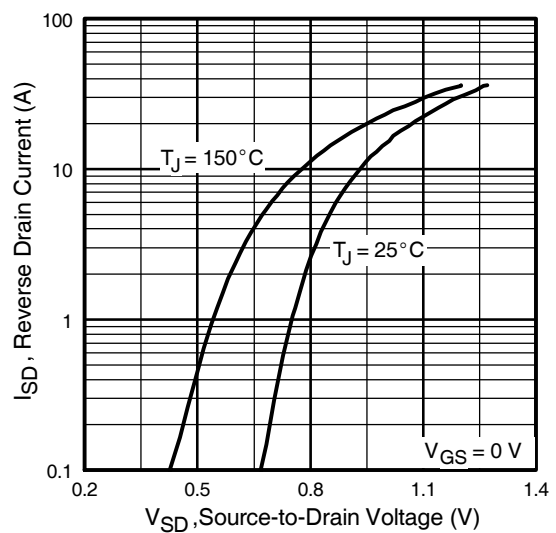
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics



**Fig 3.** Typical Transfer Characteristics



**Fig 4.** Typical Source-Drain Diode Forward Voltage

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

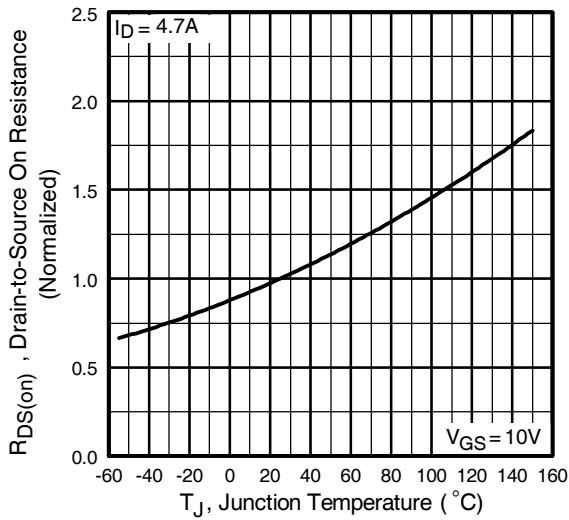


Fig 5. Normalized On-Resistance Vs. Temperature

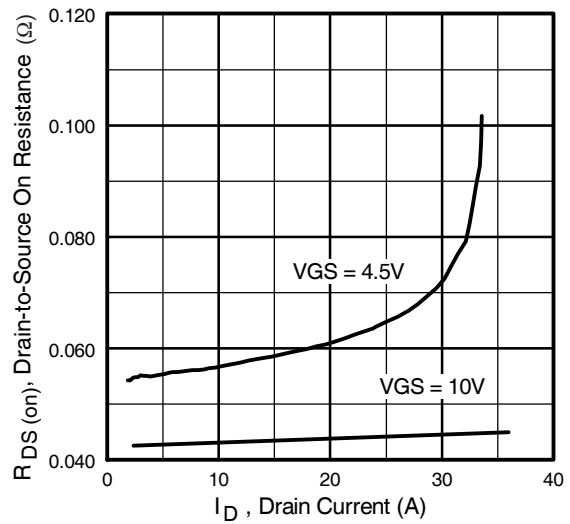


Fig 6. Typical On-Resistance Vs. Drain Current

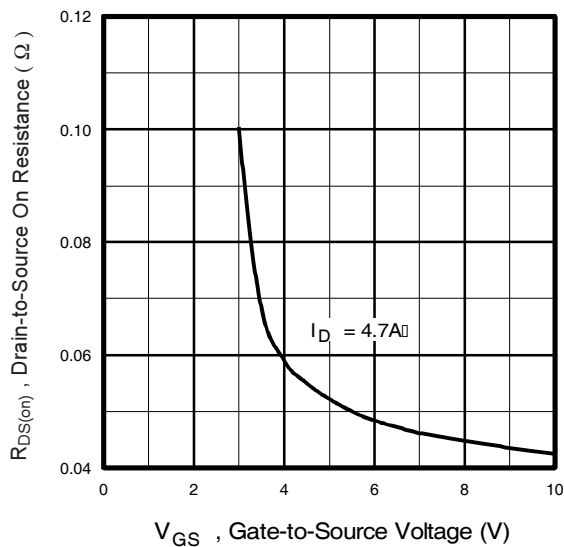


Fig 7. Typical On-Resistance Vs. Gate Voltage

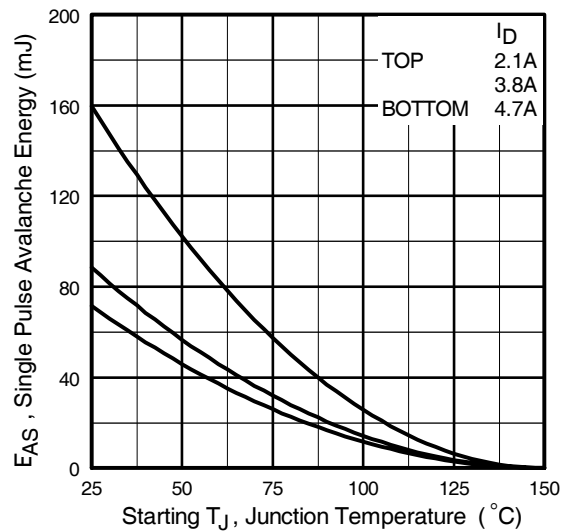


Fig 8. Maximum Avalanche Energy Vs. Drain Current

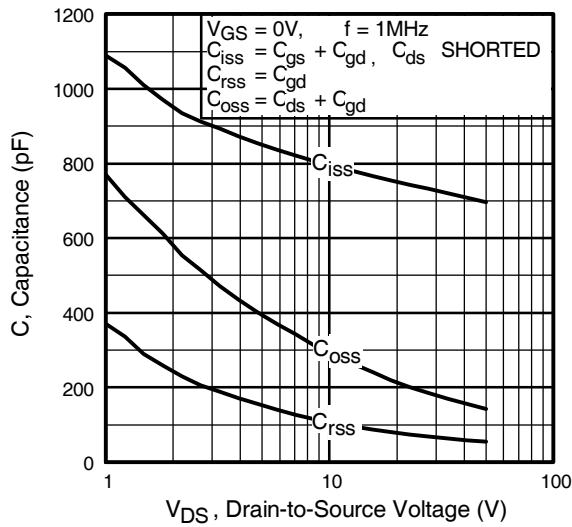


Fig 9. Typical Capacitance Vs. Drain-to-Source Voltage

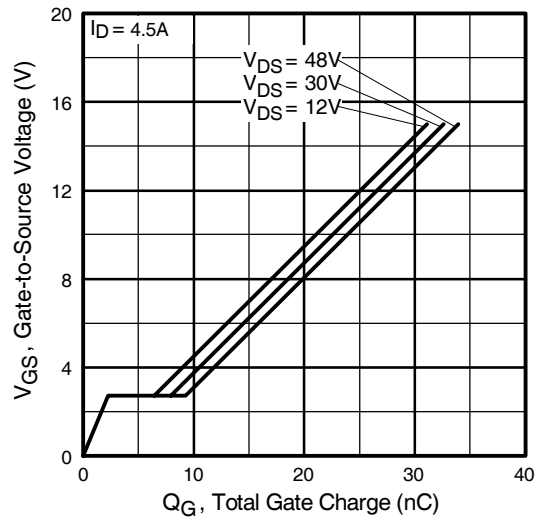


Fig 10. Typical Gate Charge Vs. Gate-to-Source Voltage

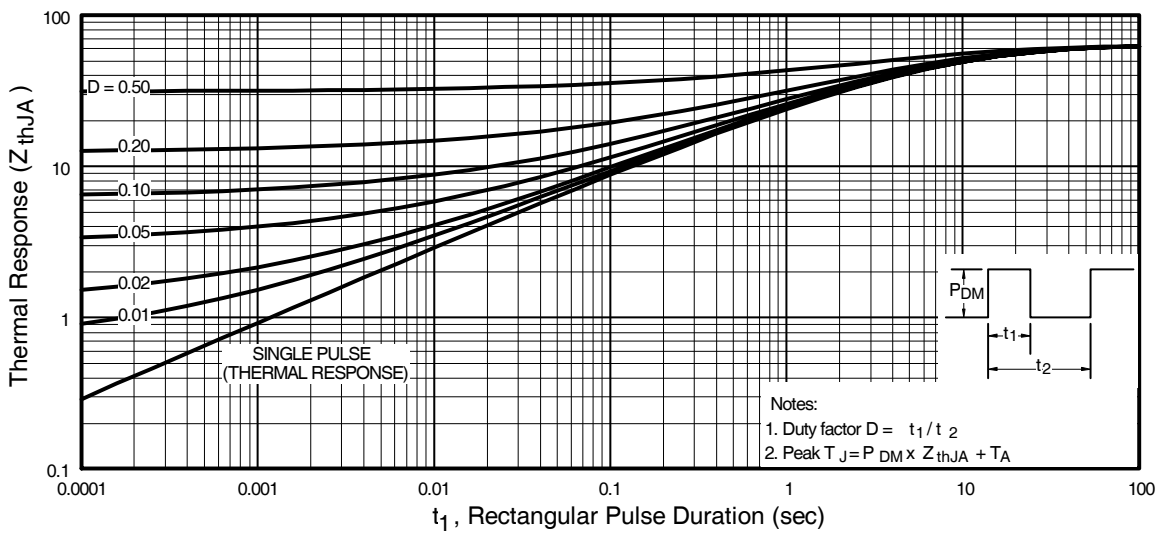
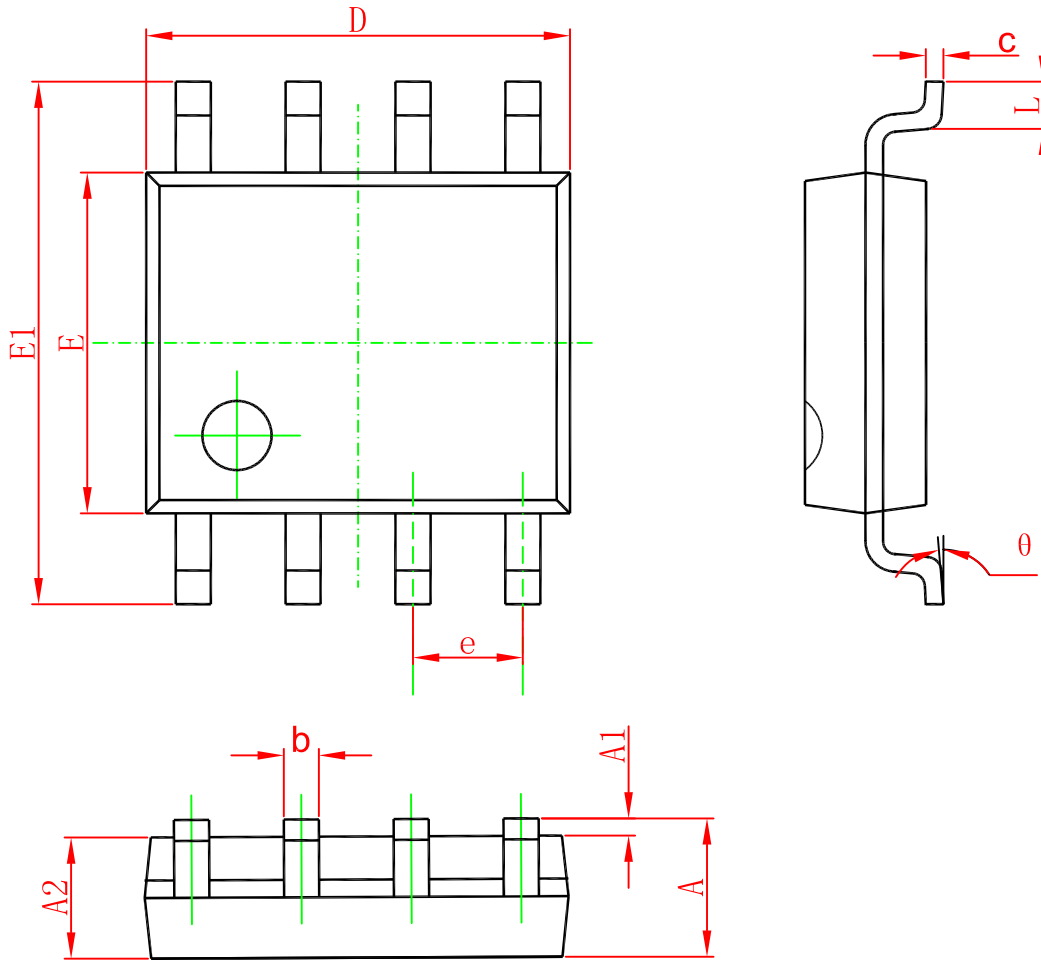


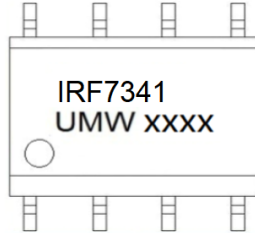
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

**Marking**



**Ordering information**

Order code	Package	Baseqty	Deliverymode
UMW IRF7341TR	SOP-8	3000	Tape and reel